

MULTIMEDIA



UNIVERSITY

STUDENT ID NO

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MULTIMEDIA UNIVERSITY

FINAL EXAMINATION

TRIMESTER 2, 2016/2017

EEE1026 – ELECTRONICS II

(All Sections / Groups)

02 MARCH 2017

02:30 p.m. - 04:30 p.m.

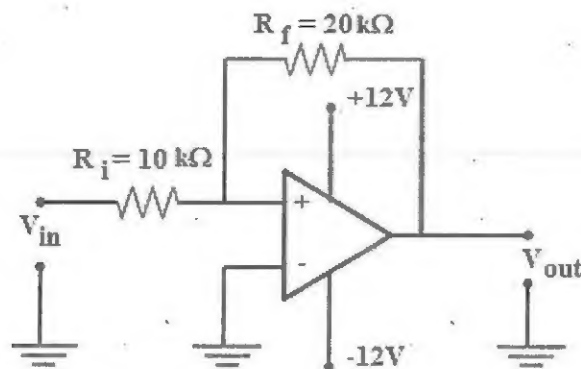
(2 Hours)

INSTRUCTION TO STUDENTS

1. This Question paper consists of 8 pages including cover page and **List of Equations** with 4 Questions only.
2. Attempt **ALL FOUR** questions. All questions carry equal marks and the distribution of the marks for each question is given.
3. Please print all your answers in the answer Booklet provided.

QUESTION 1

- (a) The Junction Field-Effect Transistor (JFET) is a fundamental electronic device that can be used as an electronic switch, which can also be constructed into amplifier.
- (i) Describe TWO methods to control the current flow in the operation of the JFET. [4 marks]
- (ii) Describe FOUR advantages of the JFET compared to Bipolar Junction Transistors (BJTs). [8 marks]
- (b) Refer to the circuit shown in Figure Q1(b), where the circuit output voltage has a 1V loss.

**Figure Q1(b)**

- (i) Compute the voltage value of the upper trigger point (UTP). [4 marks]
- (ii) Compute the voltage value of the lower trigger point (LTP). [4 marks]
- (iii) If the input voltage, V_{in} is a sinusoidal signal with peak-to-peak voltage, $V_{pp} = 30\text{V}$. Sketch the output voltage, V_{out} waveform with respect to its input voltage, V_{in} waveform. [5 marks]

Continued ...

QUESTION 2

- (a) The junction Field Effect Transistor (JFET) Small signal model is shown in Figure Q2(a), with $R_G = 20k\Omega$, $r_d = 30k\Omega$, $R_D = 3k\Omega$, $R_L = 1k\Omega$, $C_{gs} = 2.5pF$, $C_{gd} = 2pF$, $C_{ds} = 1pF$, $A_v = -8$ and $g_m = 2mA/V$.

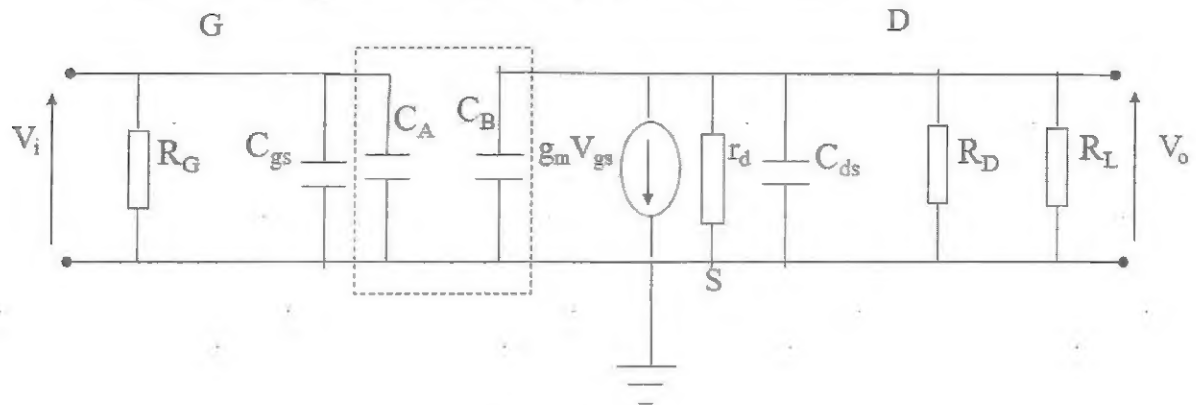


Figure Q2(a)

- (i) Compute the values of C_A and C_B . [4 marks]
 - (ii) Compute the values of the total input resistance R_{Ti} , total input capacitance C_{Ti} , total output resistance R_{To} and total output capacitance C_{To} . [5 marks]
 - (iii) Compute the values of the upper cutoff frequencies at the input and output circuits, f_{Hi} and f_{Ho} . [3 marks]
- (b) The input of the amplifier circuit is fed with an $2mV$ $10kHz$ square wave. The resultant output waveform is shown in Figure Q2 (b). Find the following:
- (i) Rise time (t_r) [1 mark]
 - (ii) The bandwidth of the amplifier [2 marks]
 - (iii) Tilt (P)% [2 marks]
 - (iv) The low cut-off frequency [2 marks]

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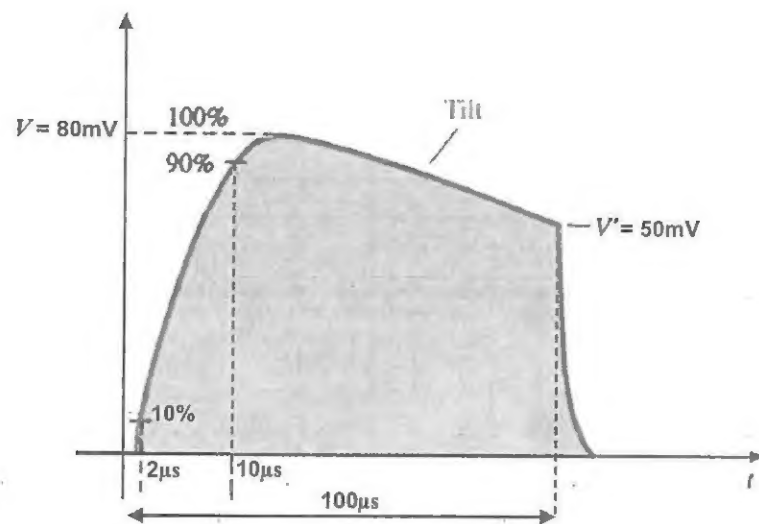


Figure Q2 (b)

- (c) A Common-Emitter BJT amplifier circuit is shown in Figure Q2 (c). Given values: $R_1=100\text{k}\Omega$, $R_2=33\text{k}\Omega$, $R_C=2.2\text{k}\Omega$, $R_E=1\text{k}\Omega$, $r_e=10\Omega$, $R_S=10\text{k}\Omega$, $V_{CC}=15\text{V}$, $\beta_{ac}=120$ and $R_{th}=7.127\text{k}\Omega$, determine the cut-off frequency of the bypass RC circuit.

[6 marks]

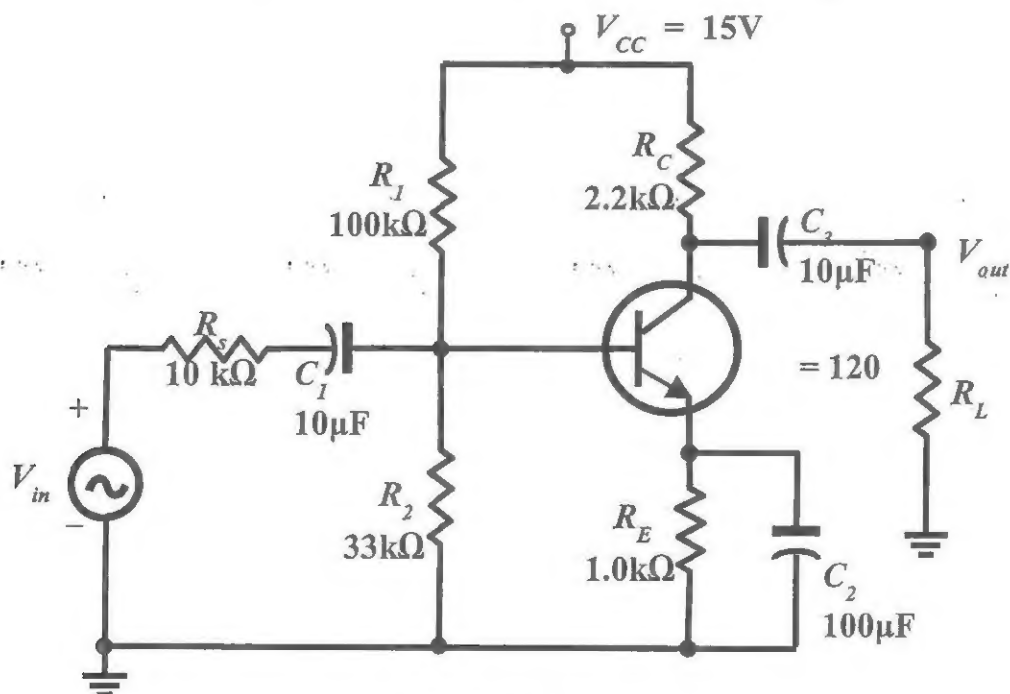


Figure Q2 (c)

Continued ...

QUESTION 3

- (a) An RC-coupled class-A power amplifier is shown in Figure Q3. The BJT amplifier has an amplification factor, $\beta = 150$. Calculate the DC load line values of $V_{CE(cutoff)}$ and $I_{C(sat)}$. [8 marks]
- (b) Calculate the following, based on Figure Q3:
- The base voltage V_B . [3 marks]
 - The voltage across emitter resistance V_E . [3 marks]
 - The collector current at the Q-point I_{CQ} . [2 marks]
 - The collector-emitter voltage at Q-point, V_{CEQ} . [3 marks]
 - The effective AC resistance of the load r_o . [2 marks]
 - $v_{ce(off)}$ and $i_{c(sat)}$. [4 marks]

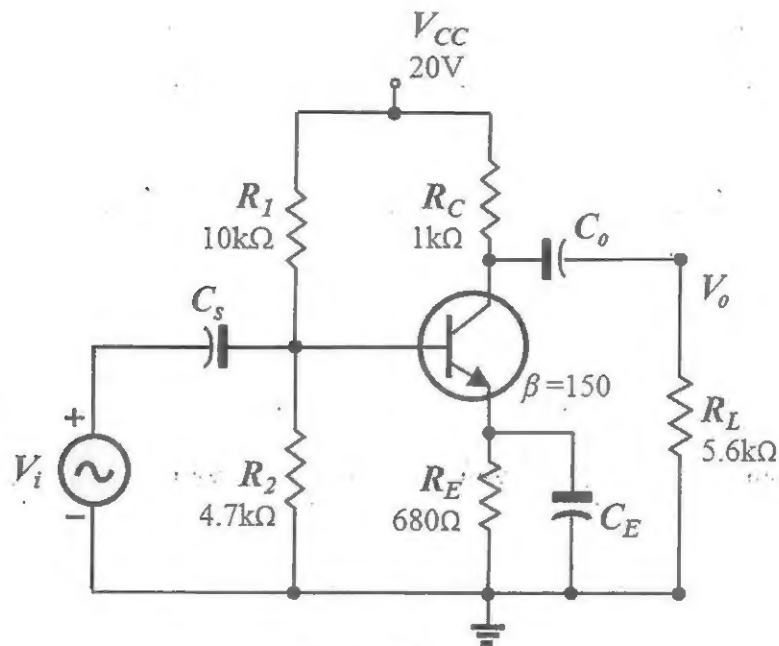


Figure Q3

QUESTION 4

For an n-channel Junction Field-Effect Transistor (JFET), the gate-source cut-off voltage, $V_{GS(OFF)}$, is -4 V and the drain saturation current, I_{DSS} is 50 mA. The drain current I_D , is 12 mA. Determine the gate-to-source voltage, V_{GS} , of the JFET.

[4 marks]

Continued ...

- (a) For an n-channel JFET amplifier circuit given in Figure Q4(b), the $V_{GS(OFF)} = -5$ V, the $I_{DSS} = 4$ mA, and the $V_{GS} = 0$ V. The drain supply voltage, $V_{DD} = 20$ V, is larger than the pinch-off voltage, V_P ($|V_{GS(OFF)}| = |V_P|$), so that the transistor operates in the saturation region. Determine the following:
- the drain current, I_D , [2 marks]
 - the drain-source voltage, V_{DS} , [3 marks]
 - the drain voltage, V_D , and [2 marks]
 - the source voltage, V_S . [2 marks]

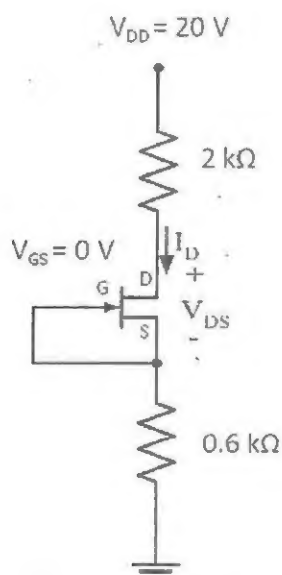


Figure Q4(b)

- (c) Refer to the circuit of the astable multivibrator shown in Figure Q4(c), with the $V_{CC} = 12$ V, $R_A = 5$ kΩ, $R_B = 2$ kΩ and $C_1 = 0.02$ μF.

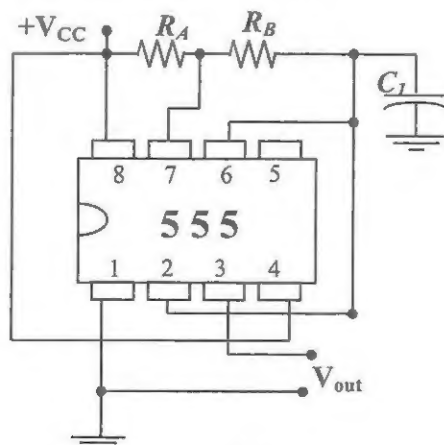


Figure Q4 (c)

- (i) Compute the value of pulse width, T_1 . [2 marks]
- (ii) Compute the value of space width, T_2 . [2 marks]
- (iii) Compute the value of free running frequency, f_o . [3 marks]
- (iv) Compute the value of the duty cycle, D . [3 marks]
- (v) Design the multivibrator by computing the new value of resistor, R_A , if the ratio of space width/pulse width, $T_2/T_1 = 0.9$. [2 marks]

End of Questions

Appendix

List of Equations

$$I_D = I_{DSS} \left(1 - \frac{V_{GS}}{V_{GS(OFF)}} \right)^2$$

$$UTP = \frac{-R_i}{R_f} V_{out-} \quad LTP = \frac{-R_i}{R_f} V_{out+}$$

$$C_A = C_{gd} (1 - A_v), \quad C_B = C_{gd} (1 - 1/A_v)$$

$$f_{Hi} = \frac{1}{2\pi R_{Ti} C_{ii}} \quad f_{Ho} = \frac{1}{2\pi R_{To} C_{io}}$$

$$\text{Tilt}\%(P) = \frac{V - V'}{V}, \quad f_L = \frac{P}{\pi} f_s$$

$$f_{c(bypass)} = \frac{1}{2\pi (R_{iin(emitter)} \parallel R_E) C_2}$$

$$V_{CC} = I_C R_C + V_{CE} + I_E R_E$$

$$V_B = \frac{R_2}{R_1 + R_2} V_{CC}$$

$$PW = T_1 = 0.693 (R_A + R_B) C_1, \quad SW = T_2 = 0.693 R_B C_1$$

$$f_o = \frac{1.44}{(R_A + 2R_B) C_1}$$

End of Paper